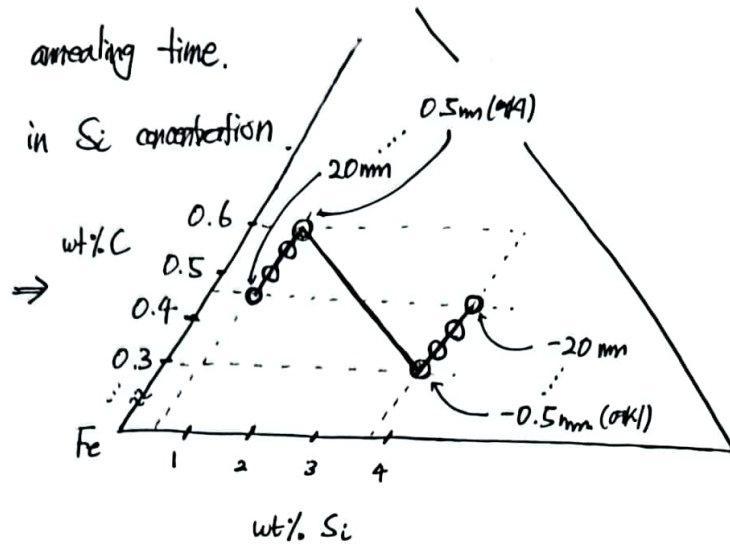
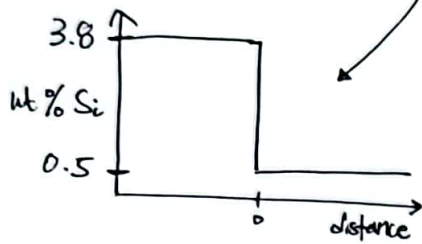


1. ① diffusion path for Bcc annealing time.

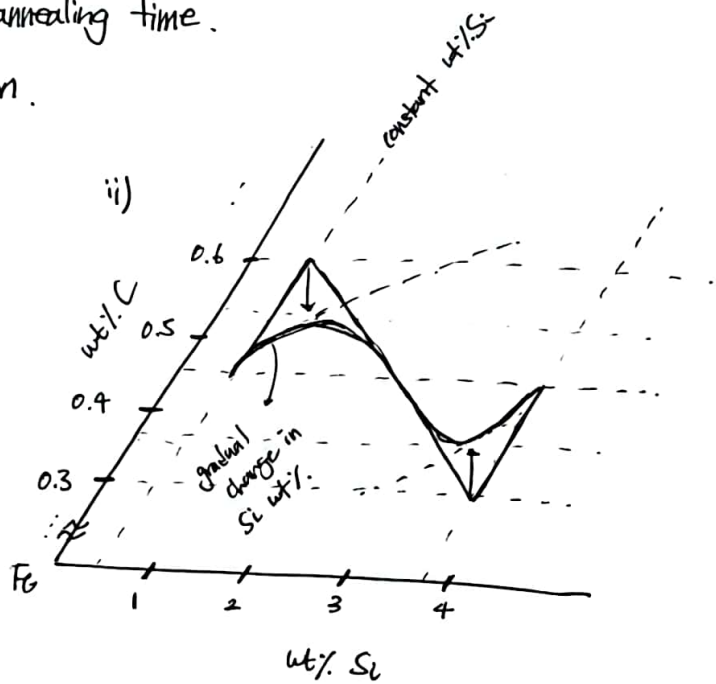
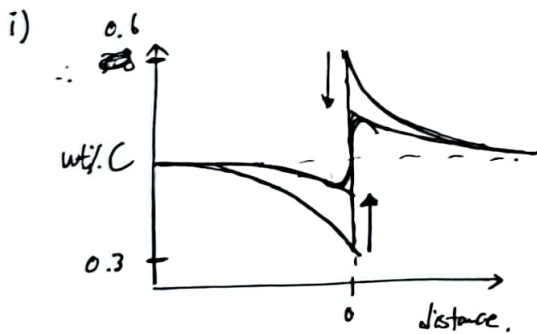
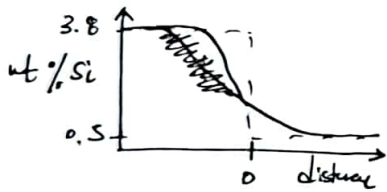
⇒ assumed abrupt change in Si concentration.



C의 wt%가 낮은 부분은 위에서 Si의 wt%가 높아  $\mu_c$ 가 높아 높음.  
C의 wt%가 높은 부분은 그 반대.

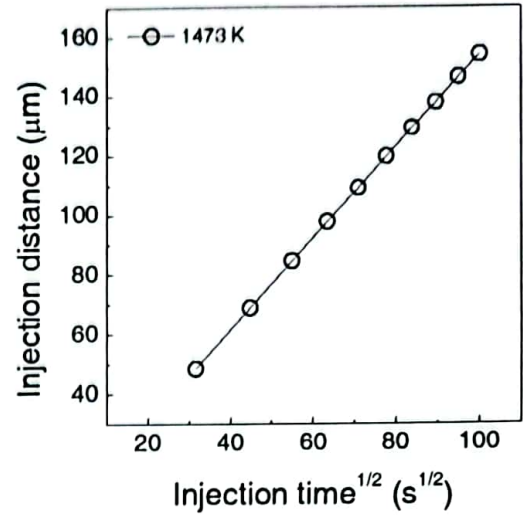
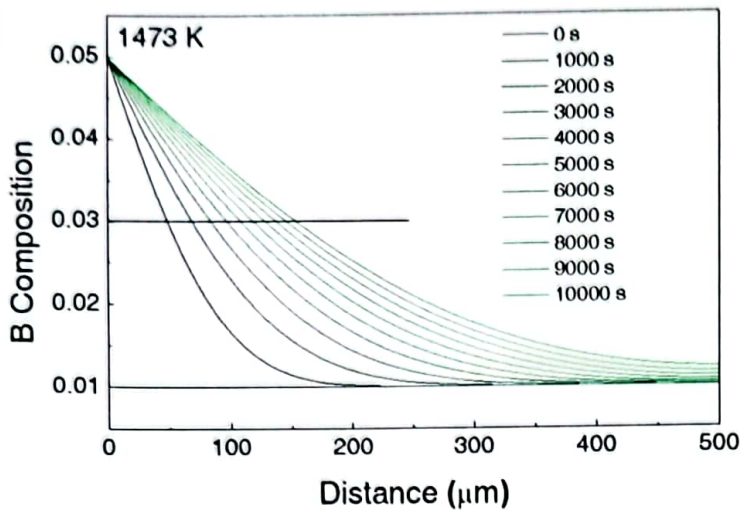
② diffusion profile & path for longer annealing time.

⇒ gradual change in Si concentration.



C의 농도차가 클수록 깊어짐.

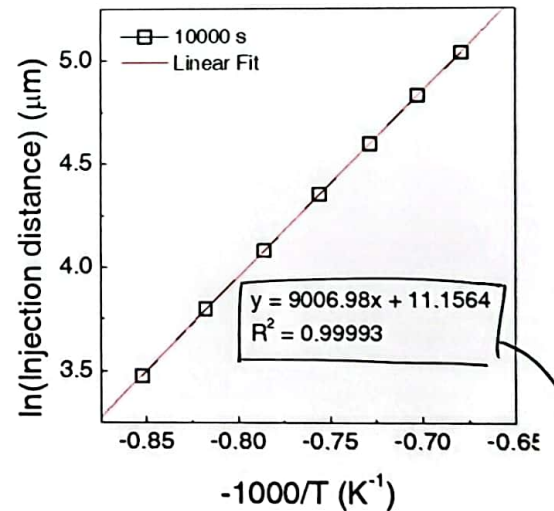
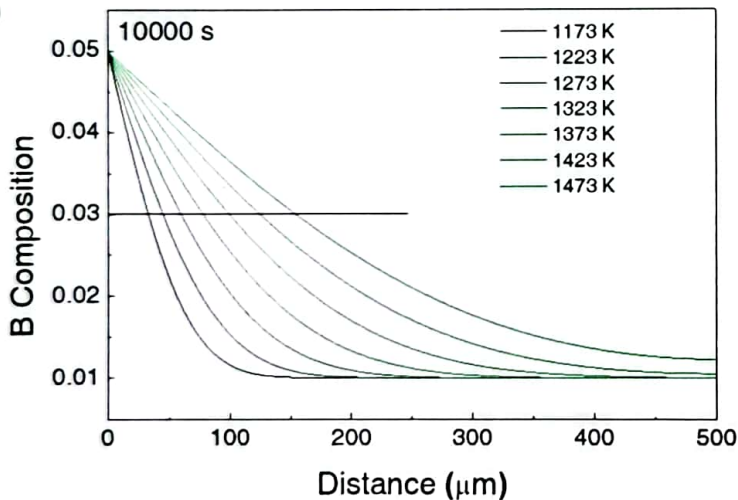
2. (a)



injection distance  $x$  가  $\sqrt{\text{injection time}}$  과 비례하는 것을 확인할 수 있다.

수업시간에 배운 이론상  $x = \sqrt{Dt}$  이기 때문에 잘 맞는다는 것을 확인할 수 있다.

(b)



$\ln x$  와  $-\frac{1}{T}$  이 선형관계임을 확인할 수 있다.

이 또한 수업시간에 배운  $x = \sqrt{Dt}$ ,  $D = D_0 \exp\left(-\frac{Q}{RT}\right)$  로 이해 가능하다.

(c)  $x = \sqrt{Dt}$ ,  $D = D_0 \exp\left(-\frac{Q}{RT}\right)$

$$x = D_0^{\frac{1}{2}} \exp\left(-\frac{Q}{2RT}\right) \rightarrow \ln x = \frac{1}{2} \ln D_0 - \frac{Q}{2R} \cdot \frac{1}{T}$$

$\therefore \ln x$  vs.  $\left(-\frac{1}{T}\right)$  graph 에서 기댓값 =  $\frac{Q}{2R}$

$\therefore Q = 9006.98 \times 2 \times 8.314 = \underline{149768 \text{ J}}$